

Fundamentals of Nanotransistors

Unit 4: Transmission Theory of the MOSFET

Lecture 4.3: MFP and Diffusion Coefficient

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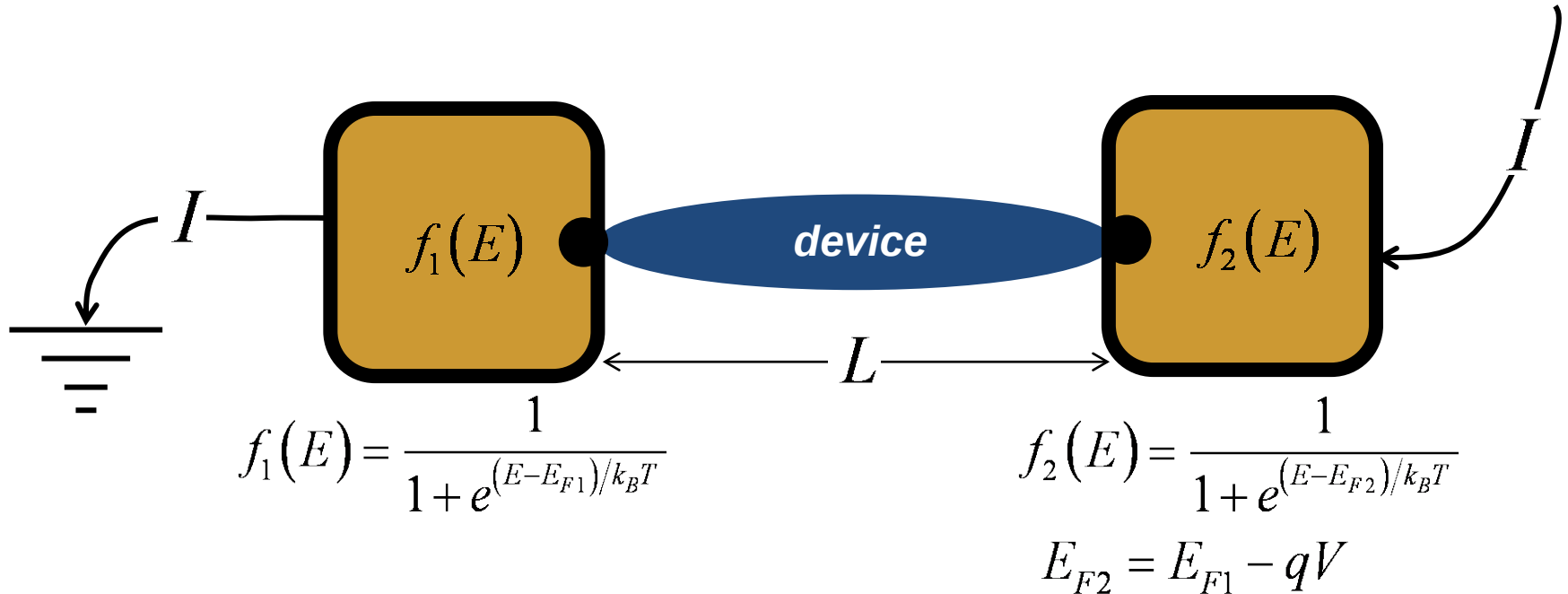
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Landauer Approach



$$I = \frac{2q}{h} \int \mathcal{T}(E) M(E) (f_1(E) - f_2(E)) dE$$

$$\mathcal{T}(E) = \frac{\lambda(E)}{L + \lambda(E)}$$



Measuring the MFP for backscattering

Question: How do we measure the MFP for backscattering?

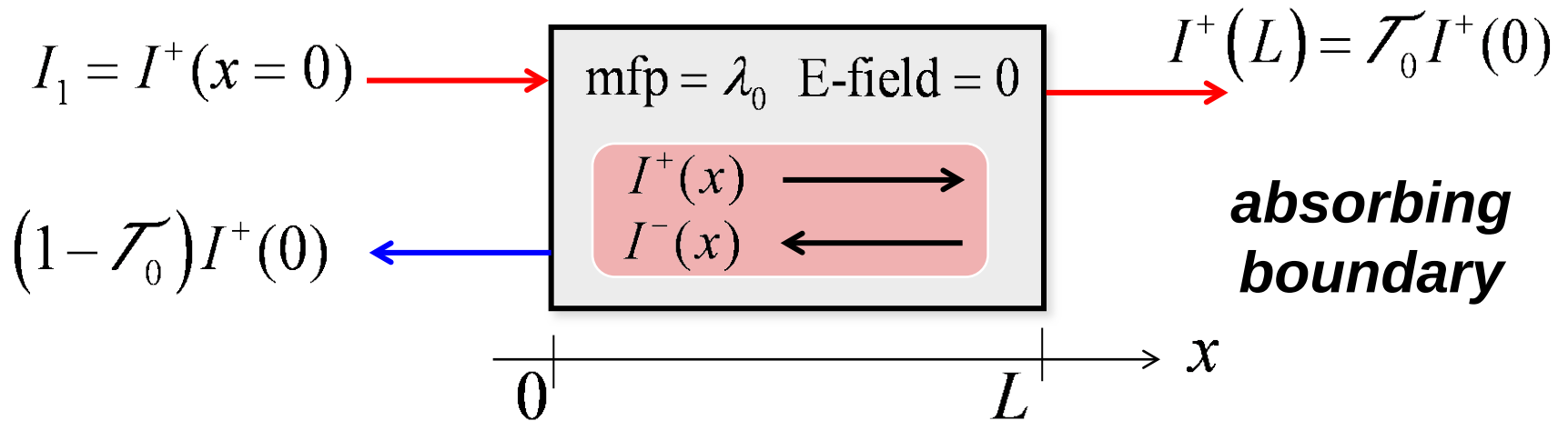
It is “easy” to measure the mobility.

Mobility and diffusion coefficient are related (near equilibrium and for non-degenerate carrier statistics) by the Einstein relation:

$$\frac{D_n}{\mu_n} = \frac{k_B T}{q}$$

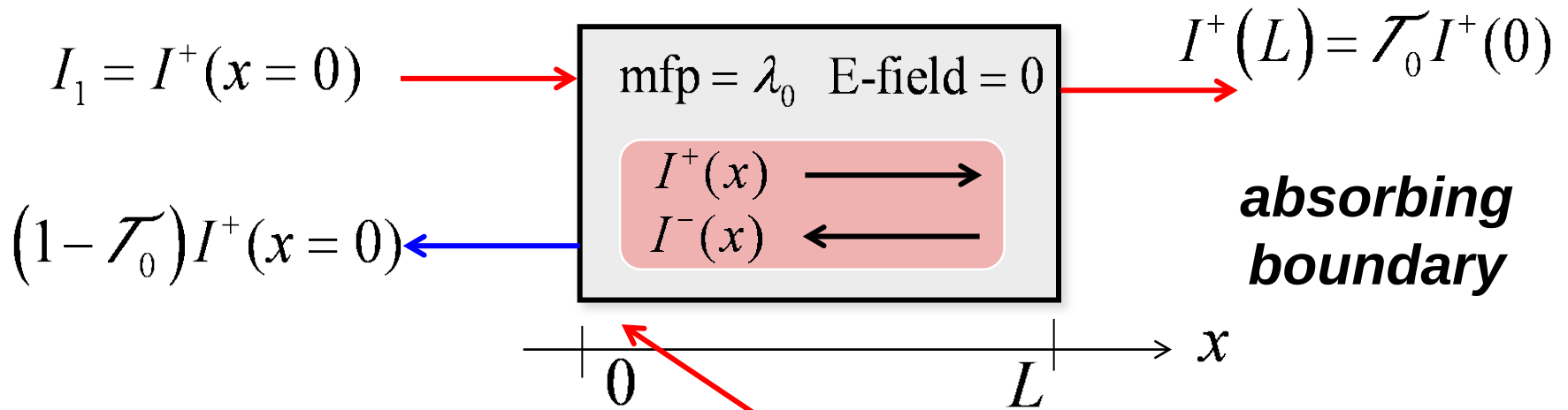
As we will show next, there is a simple relation between the MFP for backscattering and the diffusion coefficient.

The problem



We will not resolve the separate energy channels. For example, I^+ refers to the total flux integrated over all energy channels. The average MFP is λ_0 , and the average transmission is $\mathcal{T}_0$.

Carrier density at $x = 0$



$$\langle\langle v_x^+ \rangle\rangle = v_T = \sqrt{\frac{2k_B T}{\pi m^*}}$$

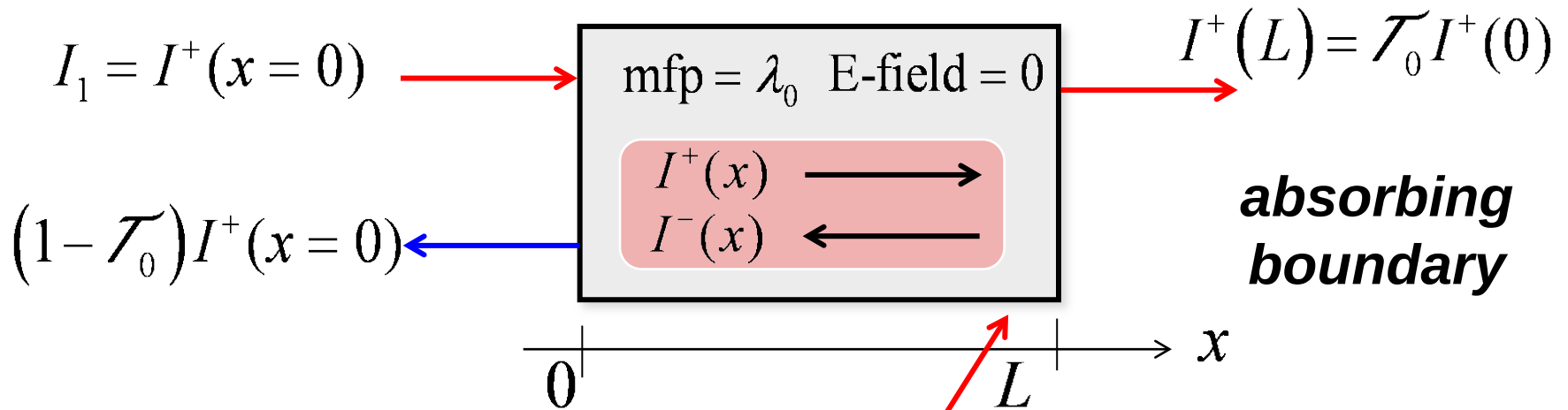
(nondegenerate)

$$n^+(0) = I^+(0) / \langle\langle v_x^+ \rangle\rangle$$

$$n^-(0) = I^-(0) / \langle\langle v_x^+ \rangle\rangle$$

$$n(0) = (2 - \mathcal{T}_0) I^+(0) / \langle\langle v_x^+ \rangle\rangle$$

Carrier density at $x = L$



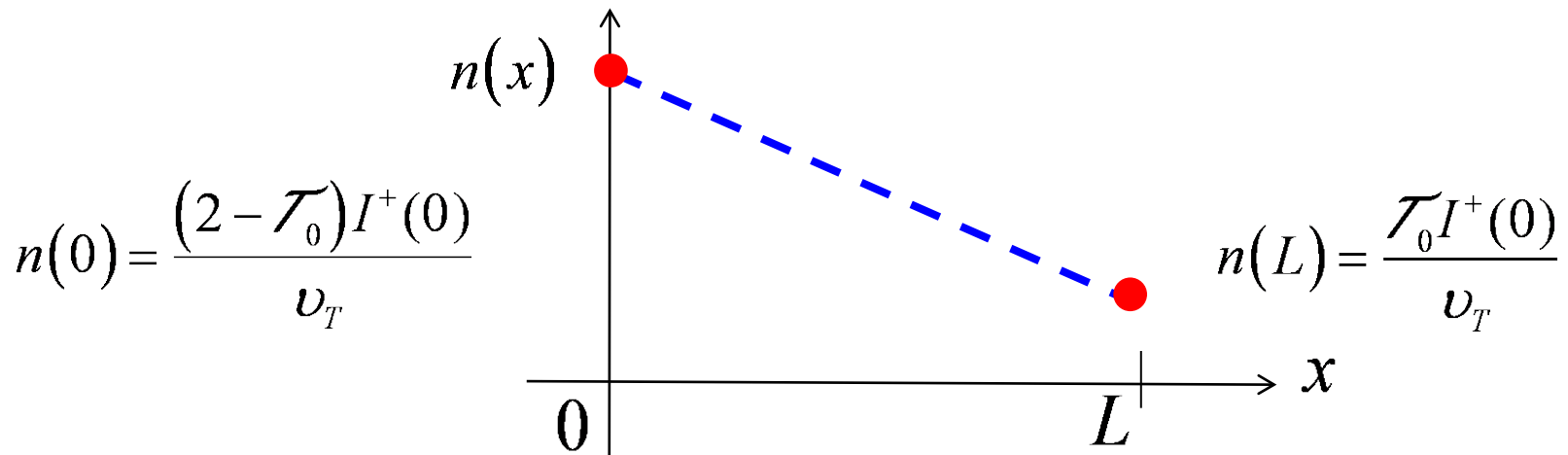
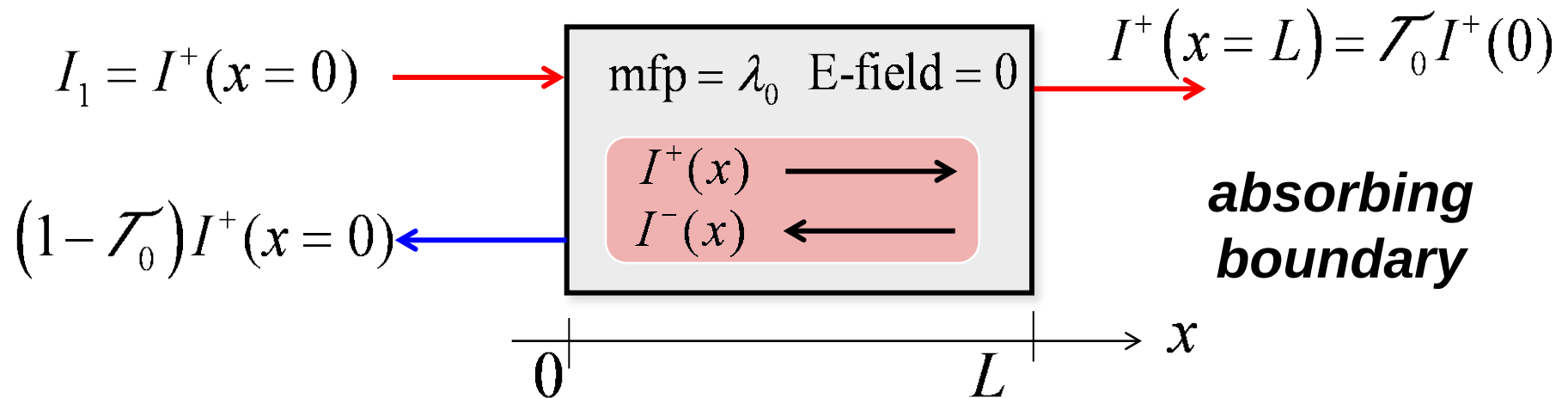
$$n^+(L) = I^+(L)/v_T$$

$$n(L) = I^+(L)/v_T$$

$$n^-(L) = 0$$

$$n(L) = \mathcal{T}_0 I^+(0)/v_T$$

Carrier density profile



Carrier density and net flux

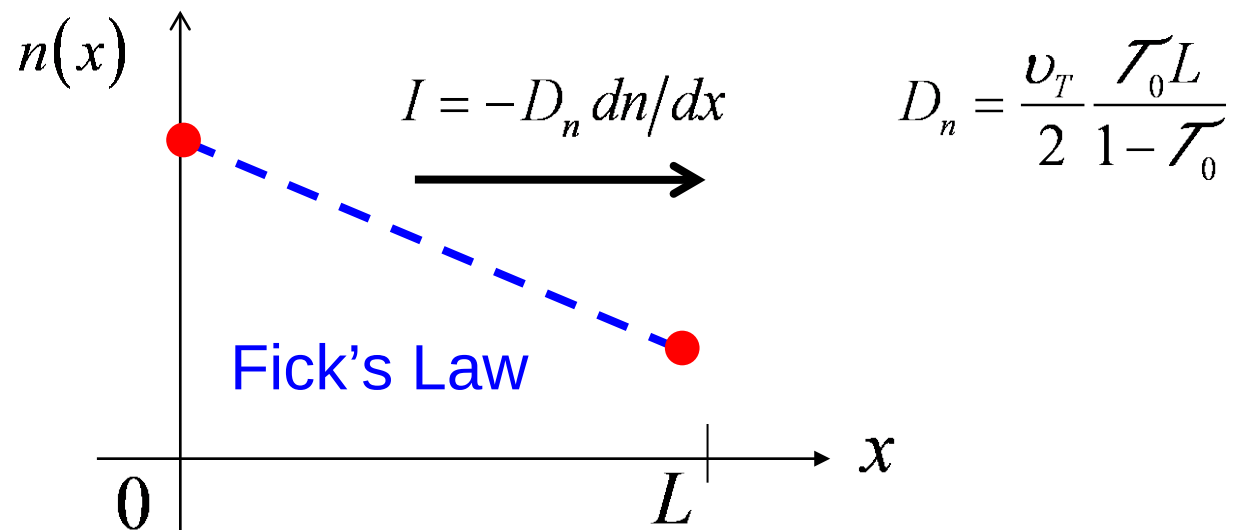
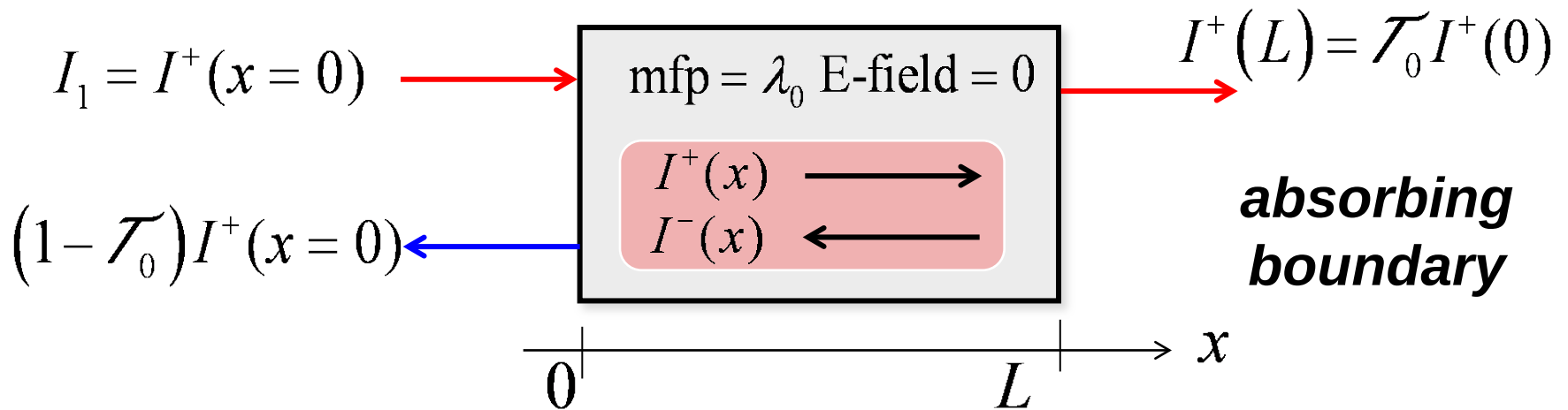
$$n(0) = \frac{(2 - \mathcal{T}_0)I^+(0)}{v_T} \quad n(L) = \frac{\mathcal{T}_0 I^+(0)}{v_T} \quad I = \mathcal{T}_0 I^+(0)$$

$$n(0) - n(L) = \frac{I^+(0)}{v_T} 2(1 - \mathcal{T}_0)$$

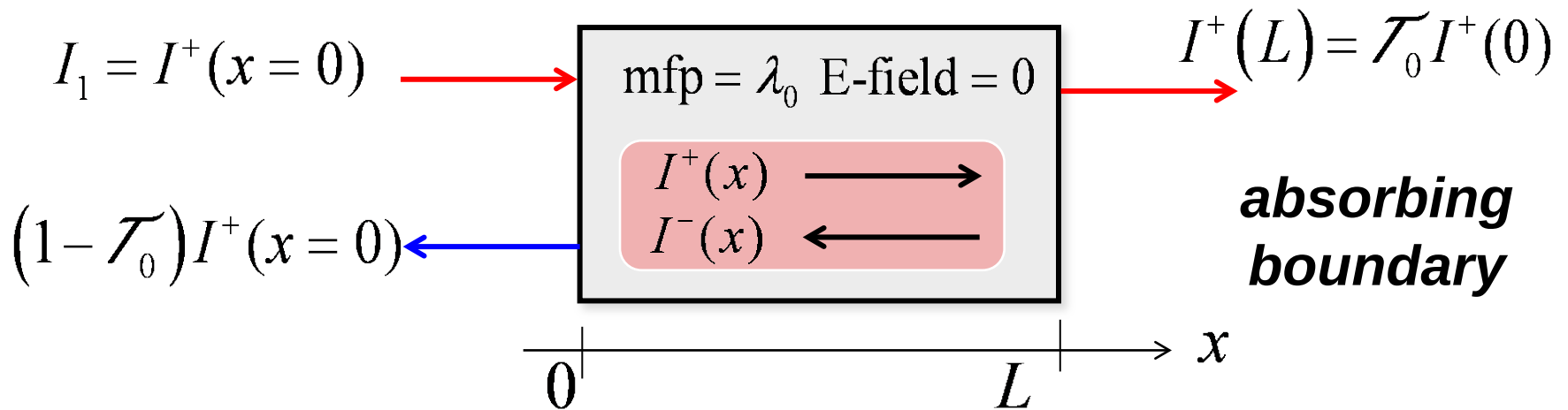
$$I = \frac{v_T}{2} \frac{\mathcal{T}_0}{1 - \mathcal{T}_0} \times [n(0) - n(L)]$$

$$I = \underbrace{\left\{ \frac{v_T}{2} \frac{\mathcal{T}_0}{1 - \mathcal{T}_0} \right\}}_{D_n} \times \underbrace{\left[\frac{n(0) - n(L)}{L} \right]}_{-dn/dx}$$

Fick's Law in a nanostructure



Fick's Law in general



$$I = -D_n \frac{dn}{dx}$$

$$\mathcal{T}_0 = \frac{\lambda_0}{\lambda_0 + L}$$

$$D_n = \frac{v_T}{2} \frac{\mathcal{T}_0 L}{1 - \mathcal{T}_0}$$

$$D_n = \frac{v_T \lambda_0}{2}$$

$$D_n = \frac{v_T \lambda_0}{2}$$

Mobility to MFP for backscattering

- 1) Given the mobility: $\mu_n \frac{\text{cm}^2}{\text{V-s}}$
- 2) Use the Einstein Relation: $\frac{D_n}{\mu_n} = \frac{k_B T}{q}$
- 3) Find diffusion coefficient: $D_n = \frac{k_B T}{q} \mu_n \frac{\text{m}^2}{\text{s}}$
- 4) Extract the MFP for backscattering: $\lambda_0 = \frac{2D_n}{v_T} \text{ m}$

Example

Consider a Si MOSFET at $T = 300$ K.

$$\mu_n = 250 \frac{\text{cm}^2}{\text{V-s}} \quad m_n^* = 0.19 m_0 \quad v_T = \sqrt{\frac{2k_B T}{\pi m_n^*}} = 1.2 \times 10^7 \text{ cm/s}$$

What is the MFP for backscattering?
(Assuming nondegenerate carrier statistics).

$$D_n = \frac{k_B T}{q} \mu_n = 0.026 \times 250 = 6.5 \frac{\text{cm}^2}{\text{s}}$$

$$\lambda_0 = \frac{2D_n}{v_T} = \frac{2 \times 6.5}{1.2 \times 10^7} = 10.8 \text{ nm} \quad \checkmark$$

Example 2

Consider a III-V HEMT at $T = 300$ K.

$$\mu_n = 12,500 \frac{\text{cm}^2}{\text{V-s}} \quad m_n^* = 0.022 m_0 \quad v_T = \sqrt{\frac{2k_B T}{\pi m_n^*}} = 3.6 \times 10^7 \text{ cm/s}$$

What is the MFP for backscattering?
(Assuming MB statistics).

$$D_n = \frac{k_B T}{q} \mu_n = 0.026 \times 12,500 = 325 \frac{\text{cm}^2}{\text{s}}$$

$$\lambda_0 = \frac{2D_n}{v_T} = \frac{2 \times 325}{3.6 \times 10^7} = 153 \text{ nm} \quad \checkmark$$

Key point of Lecture 4.3

The diffusion coefficient is directly related to the MFP for backscattering.

$$D_n = \frac{v_T \lambda_0}{2}$$

Non-degenerate carrier statistics.